



DOCUMENT CHANGE REQUEST

DCR number 412 Changes required for: N/A

Date: 2008/06/18

Date sent: 2008/06/18

Originator: Aissa nehdi

Organisation: CNES

Status: IMPLEMENTED

Title: Transistors Low Power NPN, based on type 2N3700

Number: 5201/004

Issue: 2

Other documents affected:

Page:

2.4.1 Room Temperature Electrical Measurements
page 10

Paragraph:

2.4.1 Room Temperature Electrical Measurements
page 10

Original wording:

Proposed wording:

VCE(sat)² ,Collector-Emitter saturation Voltage
Test Conditions : I_c = 500mA; I_b =50mA

Justification:

typing error

Attachments:

N/A

Modifications:

N/A

Approval signature:

Date signed:

2008-06-18